EUROPEAN PATENT OFFICE
U.S. PATENT AND TRADEMARK OFFICE

CPC NOTICE OF CHANGES 1926

DATE: AUGUST 1, 2026

PROJECT MP12943

The following classification changes will be effected by this Notice of Changes:

Action	Subclass	Group(s)
SCHEME:		
Titles Changed:	H10P	50/691
Indents Changed:	H10P	52/407, 52/409
Notes Modified:	H10P	SUBCLASS
DEFINITIONS:		
Definitions New:	H10P	SUBCLASS
	H10P	10/00, 14/00, 30/00, 50/00, 52/00, 54/00, 56/00, 58/00, 70/00, 72/50, 74/00, 76/00, 90/00
	B24B	37/30
	B65G	49/07
	G12B	15/00

The following subclasses/groups are also impacted by this Notice of Changes (indicate subclasses/groups outside of the project scope, such as those listed in the CRL):
B08B, B24B 37/00, B24B 37/04, B24B 37/34, B26D, B29C 64/00, B33Y, B81B, B81C, C04B 35/00, C09G, C09J 7/00, C23C, C23F, C25F, C30B, G01K, G01M 99/00, G01R, G01R 31/26, G03F 1/00, G12B 9/00, H01S, H02M, H03B 9/00, H03K, H05F, H05K 9/00, H10B 80/00, H10D, H10D 89/60, H10F 71/00, H10F 77/50, H10F 77/60, H10F 77/63, H10H 20/857, H10N 10/01, H10N 30/00, H10N 30/01, H10N 30/06, H10N 35/00, H10N 35/01, H10N 50/01, H10N 52/01, H10N 60/01

This Notice of Changes includes the following*:*

1. CLASSIFICATION SCHEME CHANGES
    - ☒ A. New, Modified or Deleted Group(s)
    - ☐ B. New, Modified or Deleted Warning(s)
    - ☒ C. New, Modified or Deleted Note(s)
    - ☐ D. New, Modified or Deleted Guidance Heading(s)
2. DEFINITIONS
    - ☒ A. New or Modified Definitions (Full definition template)
    - ☐ B. Modified or Deleted Definitions (Definitions Quick Fix)
3. ☐ REVISION CONCORDANCE LIST (RCL)

4. ☐ CHANGES TO THE CPC-TO-IPC CONCORDANCE LIST (CICL)
5. ☒ CHANGES TO THE CROSS-REFERENCE LIST (CRL)

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1. CLASSIFICATION SCHEME CHANGES

   A. New, Modified or Deleted Group(s)

SUBCLASS H10P - GENERIC PROCESSES OR APPARATUS FOR THE MANUFACTURE OR TREATMENT OF DEVICES COVERED BY CLASS H10

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
U	H10P 50/69	1	{using masks for semiconductor materials}	
M	H10P 50/691	2	{for Group IV materials or Group III-V materials}	
U	H10P 52/403	2	{of conductive or resistive materials}	
M	H10P 52/407	2	{of inorganic insulating materials}	
M	H10P 52/409	2	{of organic insulating materials}	

*N = new entries where reclassification into entries is involved; C = entries with modified file scope where reclassification of documents from the entries is involved; Q = new entries which are firstly populated with documents via administrative transfers from deleted (D) entries. Afterwards, the transferred documents into the Q entry will either stay or be moved to more appropriate entries, as determined by intellectual reclassification; T= existing entries with enlarged file scope, which receive documents from C or D entries, e.g. when a limiting reference is removed from the entry title; M = entries with no change to the file scope (no reclassification); D = deleted entries; F = frozen entries will be deleted once reclassification of documents from the entries is completed; U = entries that are unchanged.

NOTES:

- **No {curly brackets} are used for titles in CPC only subclasses, e.g. C12Y, A23Y; 2000 series symbol titles of groups found at the end of schemes (orthogonal codes); or the Y section titles. The {curly brackets} are used for 2000 series symbol titles found interspersed throughout the main trunk schemes (breakdown codes).
- U groups: it is obligatory to display the required "anchor" symbol (U group), i.e. the entry immediately preceding a new group or an array of new groups to be created (in case new groups are not clearly subgroups of C-type groups).Always include the symbol, indent level and title of the U group in the table above.
- All entry types should be included in the scheme changes table above for better understanding of the overall scheme change picture. Symbol, indent level, and title are required for all types .
- "Transferred to" column must be completed for all C, D, F, and Q type entries. F groups will be deleted once reclassification is completed.
- When multiple symbols are included in the "Transferred to" column, avoid using ranges of symbols in order to be as precise as possible.
- For administrative transfer of documents, the following text should be used: "< administrative transfer to XX>", "<administrative transfer to XX and YY simultaneously>", or "<administrative transfer to XX, YY, ...and ZZ simultaneously>" when administrative transfer of the same documents is to more than one place.
- Administrative transfer to main trunk groups is assumed to be the source allocation type, unless otherwise indicated.
- Administrative transfer to 2000/Y series groups is assumed to be "additional information".
- If needed, instructions for allocation type should be indicated within the angle brackets using the abbreviations "ADD" or "INV": <administrative transfer to XX ADD> , <administrative transfer to XX INV>, or < administrative transfer to XX ADD, YY INV, ... and ZZ ADD simultaneously>.

- In certain situations, the “D” entries of 2000-series or Y-series groups may not require a destination (“Transferred to”) symbol, however it is required to specify “<no transfer>” in the “Transferred to” column for such cases.
- For finalisation projects, the deleted “F” symbols should have <no transfer> in the “Transferred to” column.
- For more details about the types of scheme change, see CPC Guide.

C. New, Modified or Deleted Note(s)

SUBCLASS H10P - GENERIC PROCESSES OR APPARATUS FOR THE MANUFACTURE OR TREATMENT OF DEVICES COVERED BY CLASS H10

Type*	Location	Old Note	New/Modified Note
M	H10P	1. This subclass covers processes or apparatus specially adapted for the manufacture or treatment of devices, or parts thereof, covered by class H10, which are generically applicable to these devices. 2. Attention is drawn to the following: a. a. processes or apparatus specially adapted for the manufacture or treatment of devices, or parts thereof, which are covered by a single subclass of H10B-H10N, are classified in the subclass in question. For example, the manufacture of a transistor is classified in subclass H10D; b. b. processes or apparatus specially adapted for the manufacture or treatment of generic packages, interconnections, connectors or other constructional details of devices, which are covered by subclass H10W, are classified in the subclass in question. For example, the formation of a copper pillar bump connector is classified in subclass H10W.	1. This subclass covers processes or apparatus specially adapted for the manufacture or treatment of devices, or parts thereof, covered by class H10, which are generically applicable to these devices. 2. Attention is drawn to the following: a. processes or apparatus specially adapted for the manufacture or treatment of devices, or parts thereof, which are covered by a single subclass of H10B - H10N, are classified in the subclass in question. For example, the manufacture of a transistor is classified in subclass H10D; b. processes or apparatus specially adapted for the manufacture or treatment of generic packages, interconnections, connectors or other constructional details of devices, which are covered by subclass H10W, are classified in the subclass in question. For example, the formation of a copper pillar bump connector is classified in subclass H10W. 3. In this subclass, the periodic system used is the I to VIII group system indicated in the Periodic Table under Note (3) of section C.

*N = new note, M = modified note, D = deleted note

NOTE: The "Location" column only requires the symbol PRIOR to the location of the note. No further directions such as "before" or "after" are required.

2. A. DEFINITIONS (new)

H10P

Definition statement

This place covers:

Processes or apparatus specially adapted for the manufacture or treatment of devices, or parts thereof, covered by class H10, which are generically applicable to these devices.

Relationships with other classification places

Processes or apparatus specially adapted for the manufacture or treatment of devices, or parts thereof, which are covered by a single subclass of H10B - H10N, are classified in the subclass in question. For example, the manufacture of a transistor is classified in subclass H10D.

Processes or apparatus specially adapted for the manufacture or treatment of generic packages, interconnections, connectors or other constructional details of devices, which are covered by subclass H10W, are classified in that subclass. For example, the formation of a copper pillar bump connector is classified in subclass H10W.

References

Application-oriented references

Examples of places where the subject matter of this place is covered when specially adapted, used for a particular purpose, or incorporated in a larger system:

Electronic memory devices	H10B
Inorganic electric semiconductor devices	H10D
Inorganic semiconductor devices sensitive to infrared radiation, light, electromagnetic radiation of shorter wavelength or corpuscular radiation	H10F
Inorganic light-emitting semiconductor devices having potential barriers	H10H
Organic electric solid-state devices	H10K
Electric solid-state devices not otherwise provided for	H10N

Informative references

Attention is drawn to the following places, which may be of interest for search:

Processes or apparatus specially adapted for the manufacture or treatment of generic packages, interconnections, connectors or other constructional details of devices	H10W

Glossary of terms

In this place, the following terms or expressions are used with the meaning indicated:

bipolar	refers to semiconductor technology that involves multi-carrier-type operation, i.e. which simultaneously uses both electrons and holes as charge carriers
body	the region of semiconductor (resp. solid-state) material(s) within which, or at the surface of which, the physical effects that are characteristic of the device occur, and any bordering semiconductor (resp. solid-state) material(s) that are contiguous with this region. Examples: in a field-effect transistor [FET], the physical effects occur in the channel region between the source and the drain. The semiconductor body includes the channel region, the source and drain regions, and any contiguous semiconductor material; in a light-emitting diode [LED], the physical effects occur at a junction of active semiconductor layers. The semiconductor body includes these active semiconductor layers and any contiguous semiconductor layers, such as buffer layers, possibly a growth substrate, etc., that are between the cathode and anode electrodes;

	in a thermoelectric device, the solid-state body includes all solid-state materials in the path of current between the electrodes.
chip	a piece of a wafer or a substrate that has been processed to contain devices therein or thereon. The expression "diced chip" refers to the result of dicing a wafer or a substrate into a plurality of chips, whereas "undiced chip" refers to a chip before dicing or with no dicing.
component	an electric circuit element (e.g. diode, transistor, LED, etc.) that is one of a plurality of elements formed in or on a common substrate, e.g. in an integrated device
container	a solid construction in which (one or more) devices are placed, or which is formed around the devices, for forming packaged devices. A container requires a partial or total enclosure and it may also comprise a filling.
device	an electric circuit element (e.g. diode, transistor, LED, etc.); (depending on the context) can also refer to an integrated device (e.g. CMOS-IC, DRAM device, etc.). A device may be in the form of a bare or packaged chip.
dopant	the atoms or compounds added to a material during doping
doping	the intentional addition of a small quantity of atoms or compounds into a material to achieve a desired characteristic, e.g. to produce an n-type or p-type material
electrode	a conductive region in or on the semiconductor body or solid-state body of a device (and other than the body itself) which exerts an electrical influence on the body, irrespective of whether or not an external electrical connection is made thereto. The term covers metallic regions which exert electrical influence on the body through an insulating region (e.g. in intentional non-parasitic capacitive coupling), or inductive coupling arrangements. In a capacitive coupling

	arrangement, the dielectric region is regarded as part of the electrode. The overall conductive wiring may comprise multiple portions. In such a case, only the wiring portions that exert an electrical influence on the body are considered portions of the electrode. Examples: conductive layer(s) in direct physical contact with the body; conductive region(s) exerting an inductive coupling onto the body; a multilayer structure which exerts influence on the body through an insulating region, e.g. in intentional non-parasitic capacitive coupling.
encapsulation	an enclosure consisting of (one or more) layers, e.g. comprising organic polymers, which at least partially enclose the (one or more) devices, thereby protecting them. An encapsulation is often used to hermetically seal devices.
FET	field-effect transistor
field-effect	refers to semiconductor technology wherein a voltage applied to a gate electrode creates an electric field that allows for control of current near the interface of the gate and the body, e.g. to create an inversion channel between the source and drain of a MOSFET
individual	refers to: an electric circuit element not being an integrated device; or a component of an integrated device. Examples of individual devices include: diodes, transistors, photovoltaic cells, Josephson-junction devices, light-emitting diodes [LED], organic LEDs or a single LED component within an integrated device.
integrated circuit	an integrated device where all the electric circuit elements (e.g. diodes, transistors, LEDs, etc.) are formed in or on a common substrate, including interconnections between the elements
integrated device	a device consisting of a plurality of semiconductor or other solid-state electric circuit elements formed in or on a common substrate

interconnection	a conductive arrangement for conducting electric current from an electrode of a circuit element to another part of the circuit. Examples include metal wirings.
MIS	metal-insulator-semiconductor
MISFET	metal-insulator-semiconductor field-effect transistor
MOS	metal-oxide-semiconductor
package	the collection of all elements, which are external to the chip, that protect the chip or connect it to another object. Package therefore covers encapsulations, containers, package substrates, interposers, heatsinks or the like. Package does not include objects at a higher system level, like circuit boards and beyond, e.g. a housing in which the circuit board is enclosed.
TFT	thin-film transistor
unipolar	refers to semiconductor technology that primarily involves one type only of charge carrier, i.e. it involves either holes or electrons but not both
wafer	It can be one of the following: (a) a slice of semiconductor or electric solid-state active material. For example: a slice of silicon; a slice of a semiconducting compound, e.g. gallium nitride [GaN]; a slice of lithium tantalate [$LiTaO_3$] for superconductor applications. (b) a multilayered laminate, having at least one layer of semiconductor or electric solid-state active material, the layer being meant to be processed into devices. For example: silicon-on-insulator [SOI]; silicon-on-glass [SOG]; silicon-on-sapphire [SOS]; a composite wafer comprising silicon carbide [SiC] on polycrystalline silicon [Si] support; a layer of semiconducting nanowires on glass. A wafer is typically processed by (e.g.) deposition, etching, doping or diffusion, and is then typically diced into chips.

H10P 10/00

Definition statement

This place covers:

The bonding of wafers, substrates or parts of devices covered by class H10.

Relationships with other classification places

This group covers bonding of wafers or substrates either (i) before the step of making of any interconnections, or (ii) before the step of packaging of devices, whichever step comes first.

Aspects of bonding involving chips, package parts or interconnections, e.g. chip-on-chip bonding or chip-on-wafer bonding, are classified in subclass H10W, e.g. in group H10W 80/00.

References

Informative references

Attention is drawn to the following places, which may be of interest for search:

Debonding of wafers, substrates or parts of devices	H10P 56/00
Bonding of package parts	H10W
Direct bonding of chips, wafers or substrates	H10W 80/00

H10P 14/00

Definition statement

This place covers:

The formation of materials, e.g. in the shape of layers or pillars, over wafers or substrates or parts of devices covered by class H10.

The materials can be semiconductor, conductive, resistive or insulating.

The techniques include physical vacuum deposition, sputtering, chemical vapour deposition [CVD], physical vapour deposition [PVD], electrolytic deposition (i.e. electroplating) and electroless plating.

References

Informative references

Attention is drawn to the following places, which may be of interest for search:

Processes for applying liquids or other fluent materials	B05D 1/00
Coating by vacuum evaporation, by sputtering or by ion implantation of the coating forming material	C23C 14/00
Chemical coating	C23C 16/00 - C23C 20/00
Electroplating	C25D 3/00 - C25D 7/00
Electrolytic or electrophoretic coating	C25D 9/00 - C25D 17/00
Single crystal growth; Epitaxy	C30B

H10P 30/00

Definition statement

This place covers:

Ion implantation into wafers, substrates or parts of devices covered by class H10.

The ion implantation can take place into semiconductor materials (e.g. for doping) or into insulating materials.

References

Informative references

Attention is drawn to the following places, which may be of interest for search:

Electron-beam or ion-beam tubes for localised changing of properties of objects or for applying thin layers thereon, e.g. ion implantation	H01J 37/317

H10P 50/00

Definition statement

This place covers:

Etching specially adapted for wafers, substrates or parts of devices covered by class H10.

The etching techniques include dry etching, plasma etching, reactive-ion etching, wet etching and electrolytic etching.

The etched materials can be semiconductor, conductive, resistive or insulating materials.

References

Informative references

Attention is drawn to the following places, which may be of interest for search:

Cleaning of wafers, substrates or parts of devices	H10P 70/00
Etching, surface-brightening or pickling compositions	C09K 13/00
Etching metallic material by chemical means	C23F 1/00
Electrolytic etching or polishing	C25F 3/00

H10P 52/00

Definition statement

This place covers:

Grinding, lapping or polishing specially adapted for wafers, substrates or parts of devices covered by class H10. These processes aim to remove material from a surface of a workpiece, e.g. using loose abrasive materials.

The techniques include:

- electromechanical polishing [EMP];
- electrochemical mechanical polishing [ECMP]; and
- chemomechanical polishing [CMP].

References

Informative references

Attention is drawn to the following places, which may be of interest for search:

Machines, devices, or processes for grinding or polishing, in general	B24B
Abrasives in general	C09K 3/14
Polishing compositions	C09G 1/00
Polishing compositions containing abrasives or grinding agents	C09G 1/02

H10P 54/00

Definition statement

This place covers:

Cutting or separating of wafers or substrates having semiconductor or solid-state devices formed, or to be formed, therein or thereon. The cutting may be partial, e.g. for making a groove.

The techniques include:

- laser cutting;
- forming weakened zones for subsequent cutting or separating, e.g. by laser treatment or by ion implantation;
- sawing, e.g. using revolving or reciprocating blades;
- scoring, breaking or cleaving.

Auxiliary processes or arrangements in relation to cutting or separating of wafers or substrates having semiconductor or solid-state devices formed, or to be formed, therein or thereon.

The auxiliary processes or arrangements include:

- protecting or reinforcing the surface of wafers or substrates during cutting or separating, e.g. using adhesive tapes;
- after-treatments, e.g. removal of adhesive tapes or supports.

References

Application-oriented references

Examples of places where the subject matter of this place is covered when specially adapted, used for a particular purpose, or incorporated in a larger system:

Singulating wafers or substrates into multiple chips, i.e. dicing	H10P 58/00

Informative references

Attention is drawn to the following places, which may be of interest for search:

Etching of wafers, substrates or parts of devices	H10P 50/00
Debonding of wafers, substrates or parts of devices	H10P 56/00
Fine working, e.g. cutting, of crystalline semiconductor material; Apparatus therefor	B28D 5/00

H10P 56/00

Definition statement

This place covers:

Debonding specially adapted for wafers, substrates or parts of devices covered by class H10.

References

Informative references

Attention is drawn to the following places, which may be of interest for search:

Bonding of wafers, substrates or parts of devices	H10P 10/00
Cutting or separating of wafers, substrates or parts of devices	H10P 54/00

H10P 58/00

References

Informative references

Attention is drawn to the following places, which may be of interest for search:

Cutting or separating of wafers, substrates or parts of devices	H10P 54/00
Fine working, e.g. cutting, of crystalline semiconductor material; Apparatus therefor	B28D 5/00

Special rules of classification

When classifying in this group, any process step involving cutting or separating, which is considered to represent information of interest for search, may also be classified in group H10P 54/00.

H10P 70/00

Definition statement

This place covers:

Cleaning processes or arrangements specially adapted for the wafers, substrates or parts of devices covered by class H10.

Relationships with other classification places

This group does not cover the cleaning of package elements, package parts or other constructional details, e.g. cleaning of packages after moulding, which are covered by the related groups of subclass H10W.

References

Informative references

Attention is drawn to the following places, which may be of interest for search:

Etching of wafers, substrates or parts of devices	H10P 50/00
Cleaning in general by methods involving the use or presence of liquid or steam	B08B 3/00
Cleaning in general by methods involving the use of air flow or gas flow	B08B 5/00
Cleaning in general by electrostatic means	B08B 6/00
Detergent compositions	C11D
Electrolytic cleaning, degreasing, pickling or descaling	C25F 1/00

H10P 72/50

References

Informative references

Attention is drawn to the following places, which may be of interest for search:

Marks applied to devices, e.g. for alignment or identification	H10W 46/00

H10P 74/00

Definition statement

This place covers:

Testing or measuring during manufacture or treatment of wafers, substrates or devices covered by class H10, e.g. with the aim to detect defects, repair defects or sort defective devices.

The testing or measuring processes must be performed during the semiconductor device fabrication phase, e.g. up to and including end point determination.

References

Informative references

Attention is drawn to the following places, which may be of interest for search:

Means for detecting end-point in lapping or polishing machines	B24B 37/013
Investigating or analysing materials by determining their chemical or physical properties	G01N
Measuring electrical or magnetic variables	G01R
Measuring leads; Measuring probes	G01R 1/06
Testing electric properties of individual semiconductor devices after their manufacture	G01R 31/26
Testing electric properties of semiconductor devices without physical removal from the circuit of which they form part, after their manufacture	G01R 31/27
Testing electric properties of electronic circuits after their manufacture	G01R 31/28
Contactless testing of electric properties of integrated circuits after their manufacture	G01R 31/303
Marks applied to devices, e.g. for alignment or identification	H10W 46/00

H10P 76/00

References

Informative references

Attention is drawn to the following places, which may be of interest for search:

Photolithography, in general	G03F

H10P 90/00

Definition statement

This place covers:

Multistep processes for the preparation of wafers before the subsequent manufacture of semiconductor devices or solid-state devices therein or thereon.

The following specific multistep processes are included:

- wafer reinforcement.

References

Limiting references

This place does not cover:

Single-crystal growth of semiconductor ingots	C30B

Informative references

Attention is drawn to the following places, which may be of interest for search:

Fine working, e.g. cutting, of crystalline semiconductor material; Apparatus therefor	B28D 5/00

B24B 37/30

References

Informative references

Attention is drawn to the following places, which may be of interest for search:

Work supports, e.g. adjustable steadies, of grinding machines or devices	B24B 41/06
Apparatus specially adapted for handling wafers during manufacture or treatment of semiconductor or electric solid-state devices or components thereof using specially adapted carriers	H10P 72/10

B65G 49/07

References

Application-oriented references

Examples of places where the subject matter of this place is covered when specially adapted, used for a particular purpose, or incorporated in a larger system:

Specially adapted for conveying of semiconductor wafers during manufacture or treatment of semiconductor or electric solid-state devices or components	H10P 72/30

G12B 15/00

References

References out of a residual place

Examples of places in relation to which this place is residual:

Systems for cooling or ventilating dynamo-electric machines	H02K 9/00
Modifications to facilitate cooling, ventilating or heating in electric apparatus	H05K 7/20
Arrangements for cooling, heating, ventilating or temperature compensation of semiconductor or solid-state devices	H10W 40/00

5. CROSS-REFERENCE LIST (CRL)

Definitions references impacted by this revision project

Location of reference to be changed	**Referenced subclass or group to be changed**	**Section of definition**	**Action; New reference symbol; New text**
B08B	H10P 95/00	Application-oriented references	H10P 70/00
B08B	H10P 72/00	Application-oriented references	H10P 90/00
B24B 37/00	H10P	Informative references	Replace with: Grinding, lapping or polishing of semiconductor wafers or parts of semiconductor or solid-state devices H10P 52/00
B24B 37/00		Glossary of terms	Replace with: lapping; surface finishing by rubbing the surface of the work and the surface of a lapping tool, e.g. a lapping plate or lapping pad, that is mostly shaped corresponding to the work surface, against each other, mainly with loose abrasives rolling and sliding between the surfaces; the abrasives may be dispersed in a liquid medium, i.e. a slurry, or in a paste or fixed to the lapping pad.
B24B 37/04	B24B 7/228	Informative references	Replace with: Single purpose machines or devices designed for grinding plane surfaces on inorganic material, e.g. stone, ceramics, porcelain B24B 7/22
B24B 37/04	H10P 52/00	Informative references	Replace with: Grinding, lapping or polishing of semiconductor wafers or parts of semiconductor or solid-state devices H10P 52/00

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Location of reference to be changed	**Referenced subclass or group to be changed**	**Section of definition**	**Action; New reference symbol; New text**
B24B 37/34		Informative references	Insert new reference: Apparatus specially adapted for handling wafers during manufacture or treatment of semiconductor or electric solid-state devices or components thereof for conveying, e.g. between different workstations, for positioning, orientation or alignment, or for supporting or gripping H10P 72/30, H10P 72/50, H10P 72/70

B26D		Definition statement	Replace with: Cutting of non-metallic sheet material or metal foil in general; Cutting other forms of non-metallic materials not otherwise provided for; Apparatus or machines therefor; cutting members therefor • Characterised by the nature or movement of a cutting member which does not travel with the work, e.g. stationary or linearly movable cutting members reciprocating or rotating cutting members; • Characterised by the nature or movement of a cutting member which travels with the work, i.e. flying cutter, e.g. mounted on a movable arm or carriage; • Characterised by the nature of the cut made, e.g. bevelling, grooving, scoring, forming notches or splitting/separating layers by cutting; Apparatus therefor; Arrangements for operating and controlling machines or devices for cutting, cutting-out, stamping out, punching, perforating and also for severing by means other than cutting, e.g. • Means for moving the cutting member into its operative position for cutting, or for actuating the cutting member to affect the cut; • Arrangements with interrelated action between the cutting member and work feed, or between work feed and clamp or with means operable by the moving work to initiate the cutting action; Details of apparatus for cutting, cutting-out, stamping out, punching, perforating and also for severing by means other than cutting; • Means for holding, positioning, clamping or for removing cut-out material or waste; • Means for mounting or adjusting the cutting member or the stroke of the cutting member;

Location of reference to be changed	Referenced subclass or group to be changed	Section of definition	Action; New reference symbol; New text
			• Means for treating work or cutting member to facilitate cutting, e.g. by sharpening the cutting member; • Means for performing other operations combined with cutting, e.g. counting the number of cuts, conveying, weighting the cut product; • Cutting beds; • Safety devices specially adapted for cutting machines; Cutting apparatus combined with punching or perforating apparatus or with dissimilar cutting apparatus or combinations of several similar cutting apparatus.
B26D	H10P 14/38	Application-oriented references	H10P 54/00, H10P 58/00
B29C 64/00	H10P	Informative references	Replace with: Generic processes or apparatus for the manufacture or treatment of devices covered by class H10 H10P
B33Y	H10P	Informative references	Replace with: Generic processes or apparatus for the manufacture or treatment of devices covered by class H10 H10P
B81B		Relationships with other classification places	Insert the following new paragraph at the end of the existing text: Microelectronic devices and microoptical devices per se are classified in the subclasses of sections H (Electricity) and G (Physics) even if they also inherently (e.g. a microsized wire between two substrates that supports the upper substrate), or intentionally (e.g. an aerodynamically shaped microprocessor on a wing), accomplish a secondary structural function. Microelectronic devices and microoptical devices are found in particular in subclasses G02B, G11B, H01P and H10.

Location of reference to be changed	**Referenced subclass or group to be changed**	**Section of definition**	**Action; New reference symbol; New text**
B81B		Limiting references	Insert new reference: Semiconductors or other solid-state devices per se or combined with other devices formed on a common substrate H10

B81C		Relationships with other classification places	Replace with: Limits with application classes (e.g. switches H01H1/0036) If the objective problem solved by the invention is related to improving physical features of the device, or realising a given function, then the document should be classified in the application classes. For example: membrane structure for improving the sensitivity of an acceleration sensor, structure for realising a bi-stable switch, structure for increasing the oscillation frequency of an RF switch. If the objective problem solved by the invention is related to fabricating a specific or a general structure, or to a structure for solving a general problem, i.e. a problem that is not specific to a given device, then the document should be classified in B81C. For example: process for avoiding in-use stiction. Limits with Microfluidic applications The following criteria applies for classifying a document on microfluidic technology in B81C: The document describes a method for making a microfluidic device, the function of the device being not relevant for the manufacturing process. For example, a method (e.g. bonding stamped polymer layers) for making a three dimensional arrangement of channels and grooves. The document describes a process which solves a technical problem general to all kind of microfluidic devices. The following documents are not to be classified in B81C: Documents that describe a method for making a microfluidic structure which has a specific purpose, where the structure solves a problem specific to the technical field contemplated. For example, a specific arrangement of channels for mixing given liquids (belongs to B01F33/30)

Location of reference to be changed	Referenced subclass or group to be changed	Section of definition	Action; New reference symbol; New text
			Documents which describe also a manufacturing method corresponding to a microfluidic structure, while the method is not relevant to the invention (i.e. the method doesn't contribute to solve a technical problem general to the field of microfluidics). Documents that describe a process for solving a technical problem specific to the technical field contemplated. Limits with Nanotechnologies (B82B) Limit B81C vs B82B3/00: Bottom-up methods for manufacturing a nanosized structure are classified in B82B. Top-down methods for manufacturing a nanosized structure are classified in B81. A combination of both bottom-up and top-down processes should be classified in B81 and B82B. Processes or apparatus for the manufacture or treatment of microelectronic devices and microoptical devices per se are classified in the subclasses of section H, "Electricity" even if they also inherently (e.g. a microsized wire between two substrates that supports the upper substrate), or intentionally (e.g. an aerodynamically shaped microprocessor for wings), accomplish a secondary structural function. The manufacture or treatment of microelectronic devices and microoptical devices is found in particular in class H10 (e.g. subclass H10P) and subclass H01P (e.g. group H01P 11/00) respectively.
C04B 35/00		Application-oriented references	Insert new reference: Details of semiconductor or other solid-state devices characterised by the material, e.g. ceramic substrates H10W

Location of reference to be changed	**Referenced subclass or group to be changed**	**Section of definition**	**Action; New reference symbol; New text**
C04B 35/00		Glossary of terms	Replace with: ceramics; inorganic, non-metallic products obtained by a process involving a shaping step and a sintering or comparable heat treatment step, with the exclusion of cements, cermets and glasses, glazes, vitreous enamels and devitrified glass ceramics fine ceramics; ceramics having a polycrystalline fine-grained microstructure, e.g. of dimensions below 100 micrometer glass-ceramic refractories; ceramics or mortars withstanding high temperatures of at least about 1500 degrees C. For classification and search in this subclass no substantial distinction is made between the terms "refractories" and "ceramics" carbon-carbon composites; products consisting of carbon fibres in a carbon matrix are usually referred to as "carbon-carbon composites” porous materials; materials which are deliberately made porous, e.g. by adding gas-forming, foaming, burnable or lightweight additives to the composition they are made of
C09G		Definition statement	Replace with: Polishing compositions containing abrasives or grinding agents as well as polishing compositions based on aqueous dispersions. Polishing compositions based on wax. This includes compositions based on mixtures of wax and natural or synthetic resins. Polishing compositions based on non-waxy substances, e.g. natural or synthetic resins. Ski waxes.

Location of reference to be changed	**Referenced subclass or group to be changed**	**Section of definition**	**Action; New reference symbol; New text**
C09G		Relationships with other classification places	Insert new section: Subjects classified in subclass C09G are characterised by compositions that are used for polishing. Subjects classified in subclass C08L are not necessarily used for polishing. Subjects are classified in subclass C11D only when a significant amount of a detergent is present in a mixture. In all other cases (e.g. with a detergent as an auxiliary material) subjects are classified according to their use as polishing compositions. Subclasses C23F and C23G are for chemical polishing and chemical cleaning procedures, but compositions used for polishing are not considered. Class H10 consider a treatment step in the production of semiconductor devices. Methods, machines as well as compositions like Chemical Mechanical Polishing (hereinafter referred to as "CMP") slurries are classified in class H10. In a predominant number of cases CMP slurries are used in a semiconductor manufacturing step. CMP compositions used for polishing semiconductor devices are classified in group H10P 52/00. CMP compositions used for polishing devices other than semiconductor devices, e.g. optical devices such as lenses, are classified in subclass C09G.
C09G		Informative references	Insert new reference: Etching of semiconductor wafers or parts of semiconductor or solid-state devices H10P50/00
C09G	H10P 52/00	Informative references	Replace with: Grinding, lapping or polishing of semiconductor wafers or parts of semiconductor or solid-state devices H10P 52/00

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Location of reference to be changed	Referenced subclass or group to be changed	Section of definition	Action; New reference symbol; New text
C09G	H10P 52/402	Informative references	Replace with: Chemomechanical polishing of semiconductor materials H10P 52/402
C09G	H10P 52/403	Informative references	Replace with: Chemomechanical polishing of conductive or resistive materials H10P 52/403
C09G	H10P 90/129	Informative references	Replace with: Preparing bulk and homogeneous wafers by polishing H10P 90/129
C09G	H10P 95/06	Informative references	Replace with: Planarisation of inorganic insulating materials H10P 95/06
C09G	H10W 20/062	Informative references	Replace with: Manufacture or treatment of conductive parts of the interconnections by smoothing of conductive parts, e.g. by planarisation H10W 20/062
C09J 7/00	H10P 14/38, H10P 54/00	Application-oriented references	Replace with: Protecting or reinforcing the surface of semiconductor wafers or substrates for semiconductor or solid-state devices during cutting or separating, e.g. using adhesive tapes H10P 54/92, H10P 58/00
C09J 7/00	H10P 72/7402	Application-oriented references	H10P 72/70

Location of reference to be changed	**Referenced subclass or group to be changed**	**Section of definition**	**Action; New reference symbol; New text**
C09J 7/00		Glossary of terms	Replace with: adhesive film; a free-standing film or sheet of adhesive (adhesive without carrier) or coating of adhesive on a film or sheet rather than a larger substrate. For example, the adhesive as a film on a tape rather than a generic substrate disclosed as generally a non-tape or sheet entity. metal foil; a free-standing thin metal substrate as the only adhesive carrying component on which the adhesive is applied pressure-sensitive adhesive; pressure-sensitive adhesive (PSA, self-adhesive, self-stick adhesive) is adhesive which forms a bond when pressure is applied to adhere the adhesive with the adherend. No solvent, water or heat is needed to activate the adhesive. metallised plastic; metallised plastics are plastics coated with a thin layer of metal, usually aluminium. Metallisation is generally performed using physical vapour deposition, plating or thermal/cold spraying processes. This coating is much thinner than a metal foil could be made, in the range of 0.5 micrometres. heat-activated adhesive; heat-activated adhesives are designed to bond parts or components through the use of heat (over 50°C)

Location of reference to be changed	**Referenced subclass or group to be changed**	**Section of definition**	**Action; New reference symbol; New text**
C23C		Definition statement	Replace with: Hot-dipping or immersion processes and apparatus for applying the coating material in the molten state without affecting the shape. Coating by spraying, casting, by vacuum evaporation, by sputtering or by ion implantation and the different aspects of chemical coating which includes Chemical coating by decomposition of either gaseous compounds, liquid or solid compounds, solutions or suspensions of the coating forming compounds, without leaving reaction products of surface material in the coating. Coating starting from inorganic powder. Coating with metallic material characterised only by the composition of the metallic material. Chemical surface treatment of metallic materials, leaving reaction products of surface material in the coating. All coatings referred to in this subclass are either “for metallic materials” or “by metallic material,” with the exception of PVD (by vacuum evaporation, by sputtering or by ion implantation), and CVD (an aspect included in “the different aspects of chemical coating"). Solid-state diffusion into metallic material surfaces.
C23C	H10	Informative references	Replace with: Generic processes or apparatus for the manufacture or treatment of devices covered by class H10 H10P

Location of reference to be changed	**Referenced subclass or group to be changed**	**Section of definition**	**Action; New reference symbol; New text**
C23C		Glossary of terms	Replace with: metallic material; metals; alloys which are metallic composite materials containing a substantial proportion of fibers or other somewhat larger particles; alloys which are ceramic compositions containing free metal used as a binder for carbides, diamond, oxides, borides, nitrides or silicides, e.g. cermets, or other metal compounds, e.g. oxynitrides or sulfides, other than as macroscopic reinforcing agents
C23F	H10P 50/00	Informative references	Replace both entries (and delete the duplicate) with: Etching of semiconductor wafers or parts of semiconductor or solid-state devices H10P 50/00
C23F	H10P 72/00	Informative references	Replace with: Handling or holding of wafers, substrates or devices during manufacture or treatment thereof H10P 72/00
C23F	H10P 95/04	Informative references	Replace with: Planarisation of conductive or resistive materials in semiconductor devices H10P 95/04

Location of reference to be changed	Referenced subclass or group to be changed	Section of definition	Action; New reference symbol; New text
C23F		Glossary of terms	Replace with: metallic material; covers metals and alloys alloy; includes: metallic composite materials containing a substantial proportion of fibres or other somewhat larger particles; ceramic compositions bonded by free metal, containing free metal bonded to carbides, diamond, oxides, borides, nitrides or silicides, e.g. cermets, or other metal compounds, e.g. oxynitrides or sulfides, other than as macroscopic reinforcing agents. applying corrosion inhibitor; applying corrosion inhibitors to a metallic surface layer is not considered to be applying a protective coating inhibiting corrosion; a specific form of preventing corrosion, the words are not synonyms corrosion; deterioration of a metallic material due to a change of valence state caused by reactions with its environment incrustation; accumulation of deposition/precipitation of undesired solid/dense products on a metallic surface in systems in which a fluid circulation takes place, preferably a water-based fluid, e.g. deposition/precipitation of compounds of calcium, magnesium, barium or strontium (carbonates/sulphates, oxalates, phosphates, fluorides, silica, silicates, naphtelenates), iron/lead/zinc sulphide, zinc/cadmium carbonates (white rust)

Location of reference to be changed	**Referenced subclass or group to be changed**	**Section of definition**	**Action; New reference symbol; New text**
C25F		Relationships with other classification places	Insert new section: Multi-step processes for surface treatment of metallic material involving at least one process provided for in class C23 and at least one process provided for in class C25 are classified in C23F 17/00. The electrolytic or electrophoretic purification of materials is classified according to the nature of the liquid in the relevant places, e.g. A01K 63/00, C02F 1/46, C25B 15/08, C25D 21/16, C25F 7/02.
C25F		Application-oriented references	Insert new reference: Electrolytic etching of semiconductor wafers or parts of semiconductor or solid-state devices H10P 50/61
C30B	H10	Limiting references	Replace with: Production of semiconductor devices or parts thereof; Semiconductor devices characterised by their crystalline structure or particular orientation of the crystalline planes H10
G01K	H10W 40/28	Informative references	Replace with: Peltier coolers for semiconductor or solid-state devices H10W 40/28
G01K		Glossary of terms	Replace with: thermometer; includes thermally-sensitive elements not provided for in other subclasses
G01M 99/00		Definition statement	Insert new section: This group is a residual place for classifying testing of structures or of apparatus, not provided for elsewhere. Testing of particular devices or apparatus is often covered by the respective subclass provided for those devices or apparatus. Testing of particular devices or apparatus is classified in group G01M 99/00 only if there is no appropriate place for that subject matter elsewhere.

Location of reference to be changed	**Referenced subclass or group to be changed**	**Section of definition**	**Action; New reference symbol; New text**
G01M 99/00	G01R 31/00	Informative references	Replace with: Arrangements for testing electric properties; Arrangements for locating electric faults; Arrangements for electrical testing characterised by what is being tested not provided for elsewhere G01R 31/00
G01R		Limiting references	Insert new reference: Testing or measuring semiconductors or solid-state devices during manufacture or treatment H10P 74/00
G01R		Glossary of terms	Replace with: measuring properties; can also be interpreted as investigating properties instruments; electro-mechanical measuring mechanisms DUT; Device Under Test arrangements for measuring; apparatus, circuits or methods for measuring
G01R 31/26		Glossary of terms	Replace with: individual semiconductor device; basic semiconductor component or building block such as a diode or a transistor

Location of reference to be changed	**Referenced subclass or group to be changed**	**Section of definition**	**Action; New reference symbol; New text**
G03F1/00		Definition statement	Replace with: Patterned radiation modifying products that are chemically defined and have been patterned to modify radiation during imaging (e.g. masks, photomasks, reticles), preparation of such patterned radiation modifying products, similar or like products that function as mask blanks or specialised substrates, per se, for preparing such patterned radiation modifying products, processes of preparing such mask blanks or specialised substrates, per se (when not provided for elsewhere), pellicles, per se or pellicles in combination with patterned radiation modifying products, processes of preparing such pellicles (when not provided for elsewhere), containers that are specially adapted therefor, or processes of preparing the same (when not provided for elsewhere).
G03F1/00		Informative references	Insert new reference: Holographic processes or apparatus G03H
G03F 1/00		Informative references	Insert new reference: Generic processes or apparatus for the manufacture or treatment of devices covered by class H10 H10P
G12B 9/00	H10W76/10, H10W74/00	Informative references	H10W 74/00, H10W 76/00
H01S		Glossary of terms	Replace with: active medium; a medium providing for optical gain by the stimulated emission effect when excited by an excitation (pump) energy source laser; the acronym for "light amplification by stimulated emission of radiation" but it also refers, in broader sense, to any device using stimulated emission of radiation by excited atoms. Hence, for example, the expressions "semiconductor laser", "dye laser", "optical fibre laser" or "X-ray laser" pumping; the process of providing the active medium for excitation energy

H02M		Relationships with other classification places	Replace with: The individual electro-technical devices employed when converting electric power are covered by the relevant subclasses, e.g. inductors, transformers H01F, capacitors, electrolytic rectifiers H01G, mercury-vapour rectifying or other discharge tubes H01J, impedance networks or resonant circuits not primarily concerned with the transfer of electric power H03H, semiconductor devices H10. Voltage and current regulation circuits operating according to the non-switched (linear) principle are classified in subclass G05F. The subject matter of starting, regulating, electronically commutating, braking or otherwise controlling electrical machines using power converters covered by this subclass is classified in subclass H02P. Arrangements of power converters of this subclass in power distribution networks, not being concerned with the particular converter designs, are classified in subclass H02J. Measuring of circuit parameters such as currents, voltages or magnetic flux in general and not particularly intended for power converters of this subclass, is classified in subclass G01R. General mechanical arrangements of electronic components other than mechanical arrangements particularly intended for power converters of this subclass, are classified in subclass H05K. Protection circuits in general, other than those forming an integral part of power converters of this subclass are classified in subclass H02H. Enabling and disabling of power switches, other than particularly intended for power switches in power converters of this subclass, is classified in subclass H03K. Use and generation of Pulse Width Modulation schemes, other than particularly intended for power converters of this subclass, are classified in subclass H03K.

Location of reference to be changed	**Referenced subclass or group to be changed**	**Section of definition**	**Action; New reference symbol; New text**
			General testing and monitoring of power converters of this subclass are classified in subclass G01R. Power converters particularly adapted for charging batteries are classified in subclass H02J. Uninterruptible Power Supplies are classified in subclass H02J. Dynamically controlled power converters, that serve the purpose of signal amplification rather than energy supply as in this subclass, are classified in H03F. Power supply circuits particularly intended for operating light sources are classified in subclass H05B. Power supply circuits and arrangements particularly intended for computer type gear are classified in subclass G06F. Power supply circuits and arrangements particularly intended for video type gear are classified in subclass H04N. Switched capacitor power conversion circuits particularly intended for supply of semiconductor memory circuits are classified in subclass G11C. Generation of pulsed high-voltages used to generate sparks is classified in H01T, F23Q or F02P. Power converters being used in a particular application and characterised by their operation in that application, without focus on the design of power converter, are classified in the subclass relevant for the application.

Location of reference to be changed	Referenced subclass or group to be changed	Section of definition	Action; New reference symbol; New text
H02M		Glossary of terms	Replace with: SMPS; Switch Mode Power Supply. A general designation for the type of power converters where power is converted in small quantities at a very rapid pace. The energy entering into the conversion circuit or out of the conversion circuit is controlled by power switches. In an SMPS the power switches are typically operated either to be fully conducting or fully non-conducting, opposite to linear voltage regulators where the power switch is used as partly conductive. chopper; another name for a switch mode circuit. Chopper refers to that the signal (energy flow) is cut-up into small amounts. conversion; in respect of an electric variable, e.g. voltage or current, conversion means the change of one or more of the parameters of the variable, e.g. amplitude, frequency, phase or polarity PFC; Power Factor Correction. PFC relates to AC power input. Power Factor Correction is the discipline of rendering the input current sine-wave-shaped, with little harmonics and in phase with the AC input voltage. The aim is to make the AC input power load appear purely resistive for efficient use of the AC distribution network. snubber; a circuit aiming at absorbing or redirecting inductive energy generated during switched power conversion when a power switch is turned off (rendered non-conductive)

Location of reference to be changed	**Referenced subclass or group to be changed**	**Section of definition**	**Action; New reference symbol; New text**
H03B 9/00		Definition statement	Replace with: Oscillators comprising a device with transit-time effects as frequency determining element: Discharge tubes; Solid-state devices, e.g. Gunn-effect devices.
H03B 9/00		Glossary of terms	Replace with: transit-time effect; oscillation period equal to transit time
H03B 9/00		Synonyms and Keywords	Replace with: Impatt diode; IMPact ionisation Avalanche Transit-Time Schottky diode; diode formed by a metal-semiconductor junction Gunn diode; diode, typically built as monopolar homojunction exhibiting negative differential resistance
H03K		Limiting references	Insert new reference: Semiconductor devices; Electric solid-state devices not otherwise provided for H10
H05F		Definition statement	Replace with: Methods or arrangements for preventing the formation of electrostatic charges on bodies or for carrying-off these charges after formation. Use of naturally occurring electricity, e.g. lightning and static electricity.
H05F		Limiting references	Replace with: Installations of lightning conductors; Fastening thereof to supporting structure H02G 13/00

Location of reference to be changed	**Referenced subclass or group to be changed**	**Section of definition**	**Action; New reference symbol; New text**
H05F		Application-oriented references	Insert new reference sub-section: Specific applications of methods or arrangements for preventing the formation of static electricity or for carrying off these charges after their formation. For example: Garments protecting against electric shocks or static electricity A41D 13/008 Footwear with earthing or grounding means A43B 7/36 Carrying off electrostatic charges from living beings A61N 1/14 Electric elements specially adapted for carrying off electrostatic charges from vehicles B60R 16/06 Static discharge and lightning protection for aircraft B64D 45/02 Arrangements in large containers B65D 90/46 Protective earth or shield arrangements on coupling devices H01R 13/648 Devices providing for corona discharge H01T 19/00 Screening of printed circuits or components thereof against electric or magnetic fields H05K 9/00 Structural protection against electrostatic charges or discharges for semiconductor devices H10W 42/60

Location of reference to be changed	**Referenced subclass or group to be changed**	**Section of definition**	**Action; New reference symbol; New text**
H05F		Glossary of terms	Replace with, in this order: corona discharge or brush discharge; discharge from a conductor when the potential difference between it and its surroundings exceeds a certain value but is not enough to cause a spark or an arc coupling devices; devices having two or more parts specially adapted so as to be capable of ready and repeated physical engagement or disengagement, without the use of a tool for the purpose or establishing or breaking an electrical path electrostatic charge, static electricity; the expressions "electrostatic charge" and "static electricity" are used as synonyms for the electric charge at rest on the surface of an insulator or insulated body spark gaps; enclosed or non-enclosed discharge devices having cold electrodes and used exclusively to discharge a quantity of electrical energy in small time duration
H05K 9/00	H10W 42/20, H10W 72/00	Application-oriented references	Replace with: Protecting against electromagnetic or particle radiation of semiconductor devices H10W 42/20
H10B 80/00	H10W 90/00	Informative references	Replace with: Package configurations H10W 90/00
H10D	H10W 99/00	Limiting references	Replace with: Generic packages, interconnections, connectors or other constructional details of devices covered by class H10 H10W

H10D		Synonyms and keywords	Replace with: *Abbreviations:* MIS; metal-insulator-semiconductor MOS; metal-oxide-semiconductor CMIS; complementary MIS CMOS; complementary MOS DMOS; double-diffused MOS LDMOS; lateral DMOS VDMOS; vertical DMOS MNOS; metal-nitride-oxide-semiconductor IMPATT; impact ionisation avalanche transit-time TRAPATT; trapped plasma avalanche triggered transit BJT; bipolar junction transistor HEMT; high-electron-mobility transistor TFT; thin-film transistor IGFET; insulated-gate FET IGBT; insulated-gate bipolar transistor CCD; charge-coupled device CAD; computer-aided design

Location of reference to be changed	Referenced subclass or group to be changed	Section of definition	Action; New reference symbol; New text
			LSI; large-scale integration
H10D 89/60		Informative references	Insert new reference: Arrangements for thermal protection H10W 40/00
H10D 89/60	H10W 42/60, H10W 42/80	Informative references	Replace with: Arrangements for electrical protection H10W 42/60, H10W 42/80
H10F 71/00	H10P	Informative references	Replace with: Generic processes or apparatus for the manufacture or treatment of devices covered by class H10 H10P
H10F 77/50	H10W 74/00	Informative references	Replace with: Encapsulations generically applicable to semiconductor or solid-state devices H10W 74/00
H10F 77/50	H10W 76/10	Informative references	Replace with: Containers generically applicable to semiconductor or solid-state devices H10W 76/10
H10F 77/60	H10W 40/00	Informative references	Replace with: Arrangements for thermal protection or thermal control H10W 40/00
H10F 77/63	H10W 40/28	Informative references	Replace with: Peltier coolers for semiconductor or solid-state devices H10W 40/28
H10H 20/857	H10W 72/00	Informative references	Replace with: Interconnections generically applicable to semiconductor devices or packages H10W 20/40, H10W 72/00
H10N 10/01	H10P	Informative references	Replace with: Generic processes or apparatus for the manufacture or treatment of devices covered by class H10 H10P
H10N 30/00	H10P	Informative references	Delete entire reference

Location of reference to be changed	Referenced subclass or group to be changed	Section of definition	Action; New reference symbol; New text
H10N 30/01	H10P	Informative references	Replace with: Generic processes or apparatus for the manufacture or treatment of devices covered by class H10 H10P
H10N 30/06	H10P	Informative references	Replace with: Generic processes or apparatus for the manufacture or treatment of devices covered by class H10 H10P
H10N 35/00	H10P	Informative references	Delete entire reference
H10N 35/01	H10P	Informative references	Replace with: Generic processes or apparatus for the manufacture or treatment of devices covered by class H10 H10P
H10N 50/01	H10P	Informative references	Replace with: Generic processes or apparatus for the manufacture or treatment of devices covered by class H10 H10P
H10N 52/01	H10P	Informative references	Replace with: Generic processes or apparatus for the manufacture or treatment of devices covered by class H10 H10P
H10N 60/01	H10P	Informative references	Replace with: Generic processes or apparatus for the manufacture or treatment of devices covered by class H10 H10P

NOTES:

- The CRL tables above are used for changes to locations **outside** of the project scope. Changes to references in scheme titles or definitions inside the project scope will be reflected in the “scheme change” template or one of the “definition” templates.
- In addition to other changes proposed in the tables above, in the column titled “Referenced subclass or group to be changed,” **referenced** D symbols should indicate an action of “delete” or should indicate a replacement symbol and **referenced** F symbols should indicate a replacement symbol.
- When a reference is deleted, text related to that reference will also be deleted unless other references or a range of references associated with the same text remain.